

SPTECH Silicon PNP Power Transistor**2SB546****DESCRIPTION**

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V$ (Min)
- Collector Power Dissipation-
: $P_C = 30W(\text{Max}) @ T_C = 25^\circ\text{C}$
- Complement to Type 2SD401

APPLICATIONS

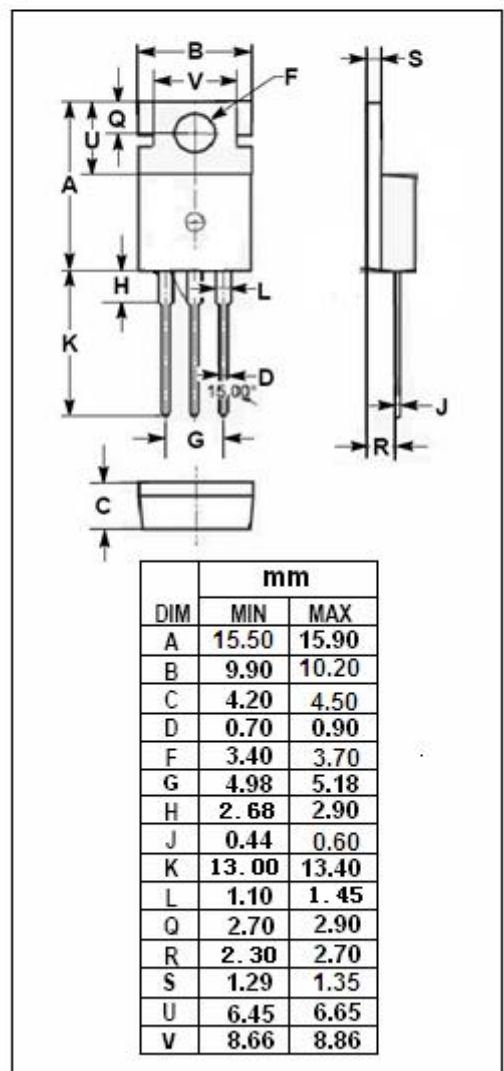
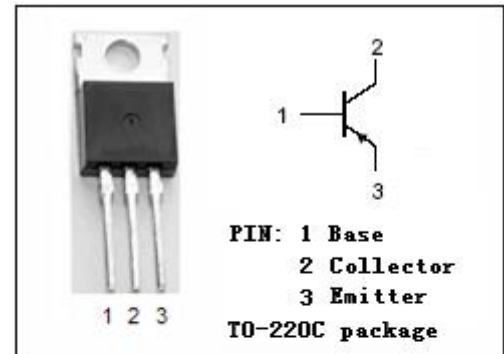
- Designed for use in line-operated color TV vertical deflection of complementary symmetry circuit.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
I_{BM}	Base Current-Peak	-1.5	A
P_C	Total Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
T_J	Junction Temperature	150	
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	78	$^\circ\text{C/W}$
$R_{th j-c}$	Thermal Resistance, Junction to Case	4.16	$^\circ\text{C/W}$



SPTECH Silicon PNP Power Transistor**2SB546****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA ; I _B = 0	-150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA			-2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -150V ; I _E = 0			-50	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-50	μ A
h _{FE}	DC Current Gain	I _C = -0.4A ; V _{CE} = -10V	40			
f _T	Current-Gain—Bandwidth Product	I _C = -0.4A ; V _{CE} = -10V		7		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1MHz		75		pF